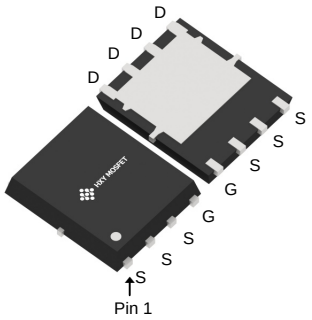
General Description

The DMT10H4M5LPS-13 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness and suitable.

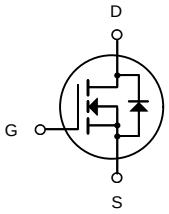


DFN5X6-8L

General Features

V_{DS} = 100V I_D = 120A

$R_{DS(ON)}$ < 4.4mΩ@ V_{GS}=10V



N-Channel MOSFET

Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMT10H4M5LPS-13	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (T_C =25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V [1]	120	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V [1]	81	A
I_{DM}	Pulsed Drain Current[2]	512	A
EAS	Single Pulse Avalanche Energy[3]	486	mJ
I_{AS}	Avalanche Current	67	A
P_D@T_C=25°C	Total Power Dissipation[4]	176	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JC}$	Thermal Resistance from Junction-to-Ambient[3]	0.8	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	56	°C/W

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	3.6	4.4	mΩ
		V_{GS}=4.5V , I_D=20A	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.0	3.0	4.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	35	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.6	---	Ω
Q_g	Total Gate Charge	V_{DS}=50V , V_{GS}=10V , I_D=20A	---	69	---	nC
Q_{gs}	Gate-Source Charge		---	24	---	
Q_{gd}	Gate-Drain Charge		---	18.5	---	
$T_{d(on)}$	Turn-On Delay Time	VGS=10V, VDD=50V, RG=3Ω, ID=20A	---	18.0	---	ns
T_r	Rise Time		---	23	---	
$T_{d(off)}$	Turn-Off Delay Time		---	37	---	
T_f	Fall Time		---	15.7	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	4102	---	pF
C_{oss}	Output Capacitance		---	592	---	
C_{rss}	Reverse Transfer Capacitance		---	19.8	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	120	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is TJ = 25°C, L = 3.0mH, IAS = 18A, VGS = 10V, VDD = 50V; 100% test at L = 0.1mH, IAS = 67A.

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

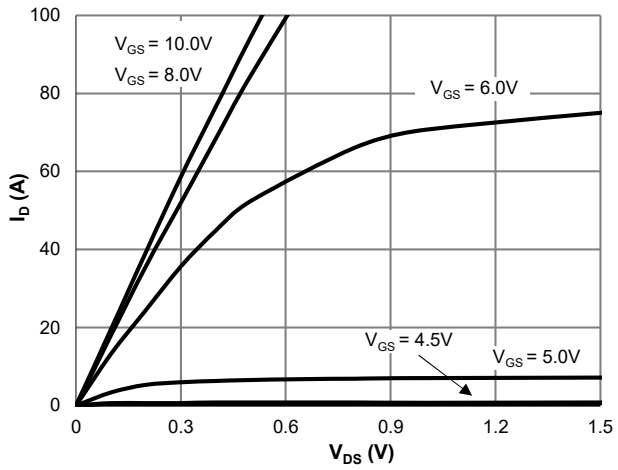


Figure 1: Saturation Characteristics

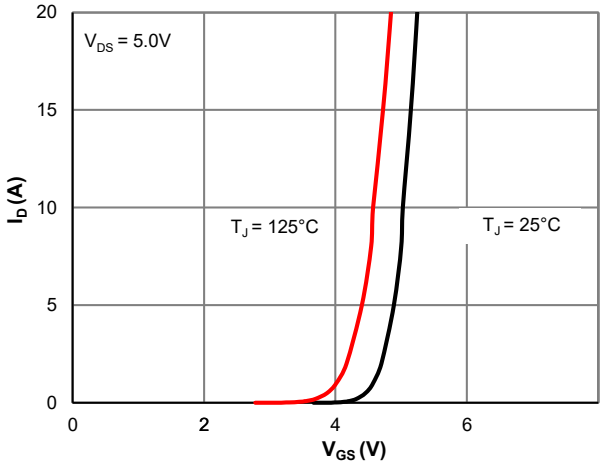


Figure 2: Transfer Characteristics

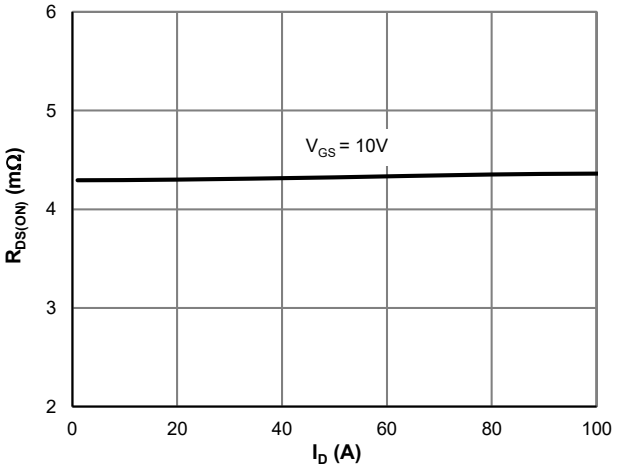


Figure 3: $R_{DS(ON)}$ vs. Drain Current

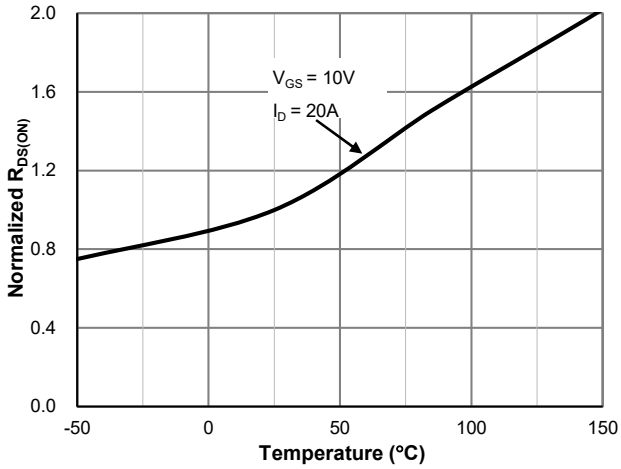


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

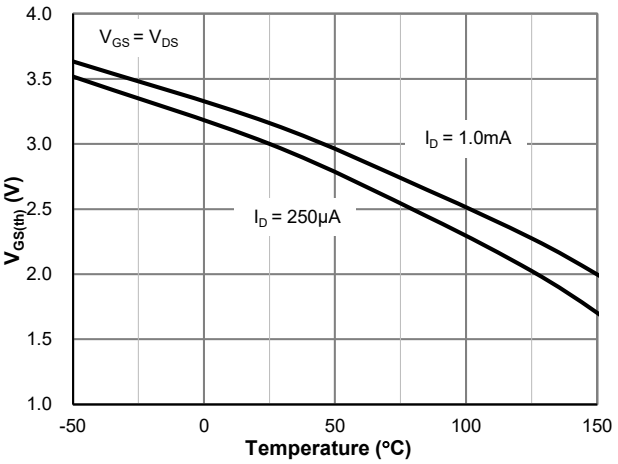


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

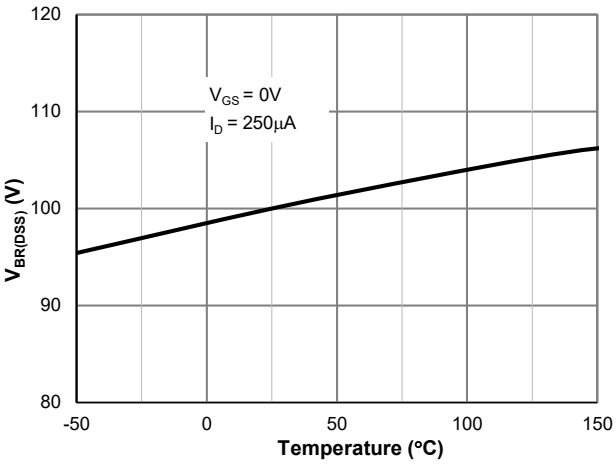


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

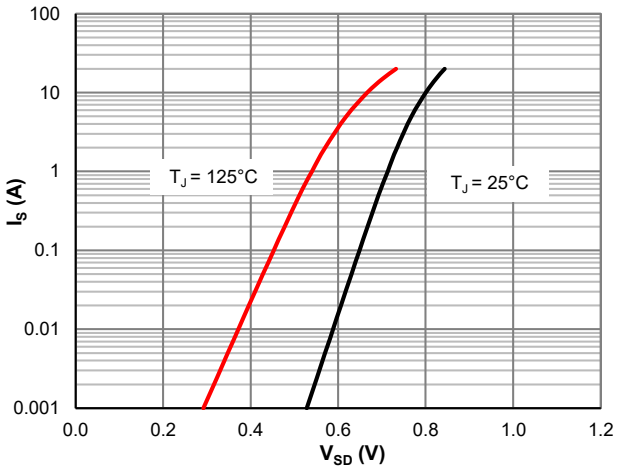


Figure 7: Body-Diode Characteristics

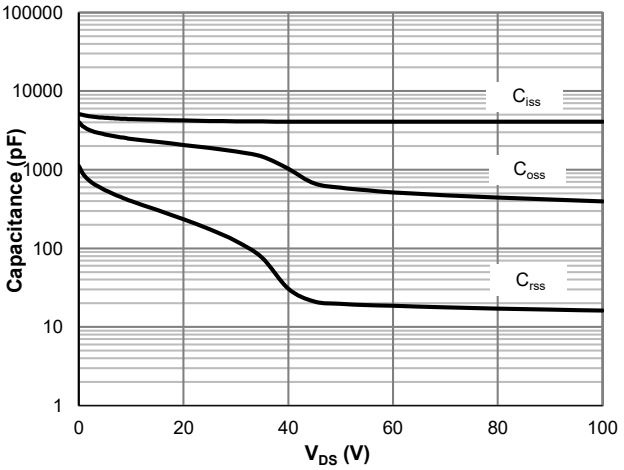


Figure 8: Capacitance Characteristics

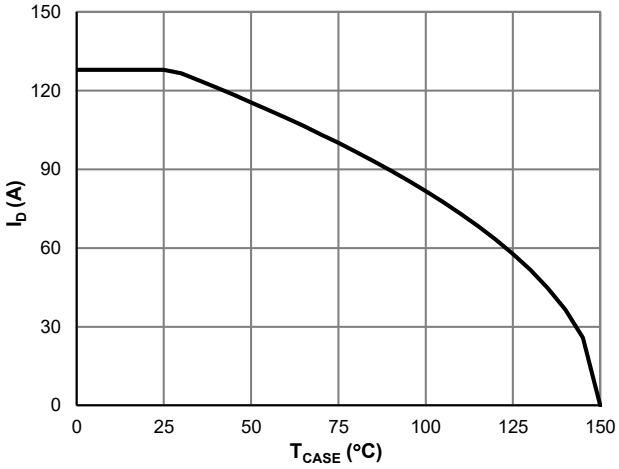


Figure 9: Current De-rating

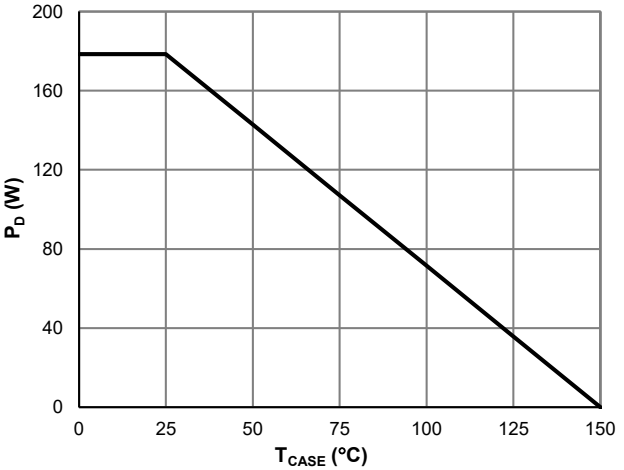


Figure 10: Power De-rating

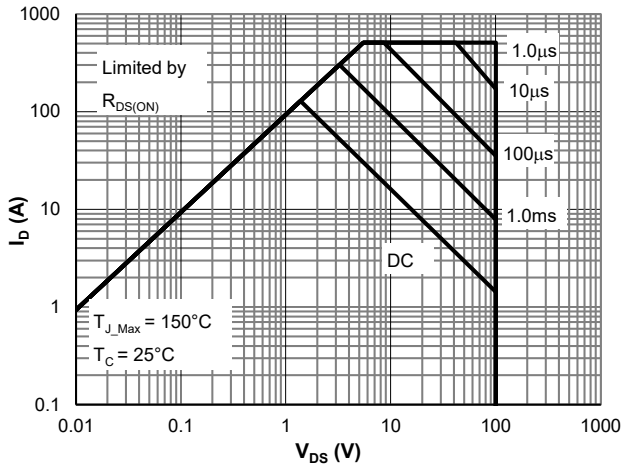


Figure 11: Maximum Safe Operating Area

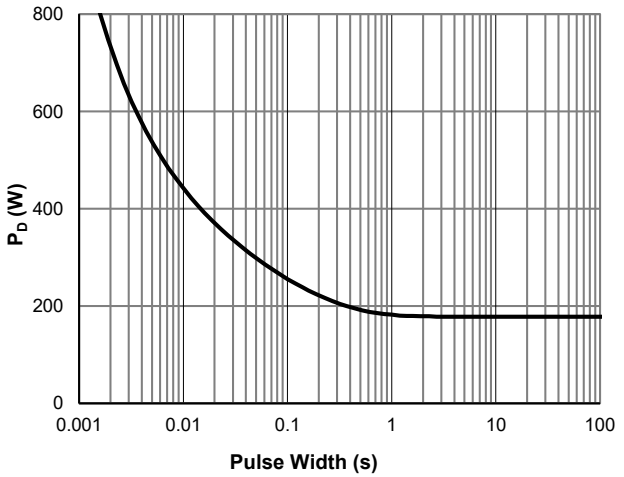


Figure 12: Single Pulse Power Rating, Junction-to-Case

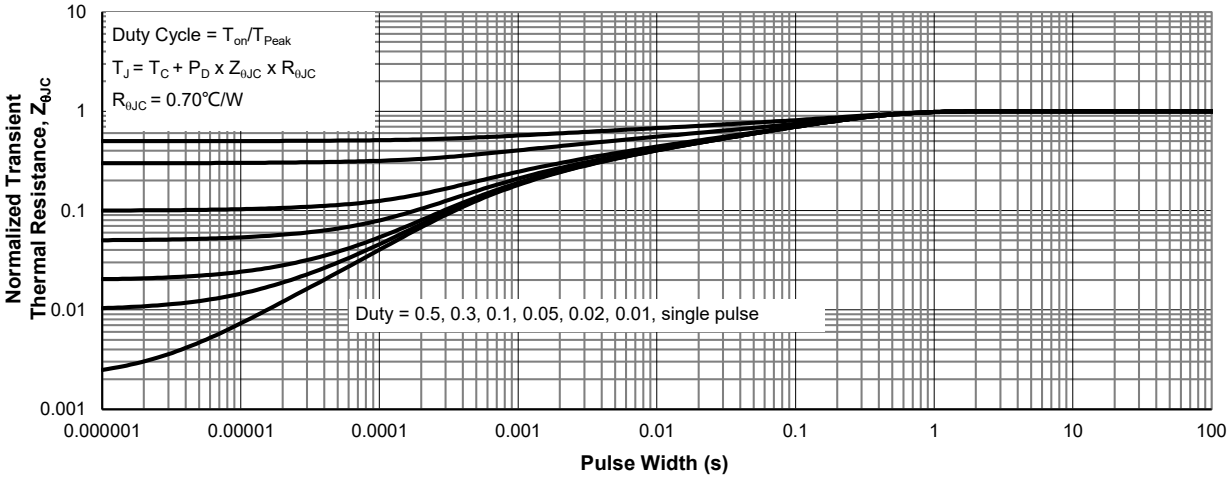
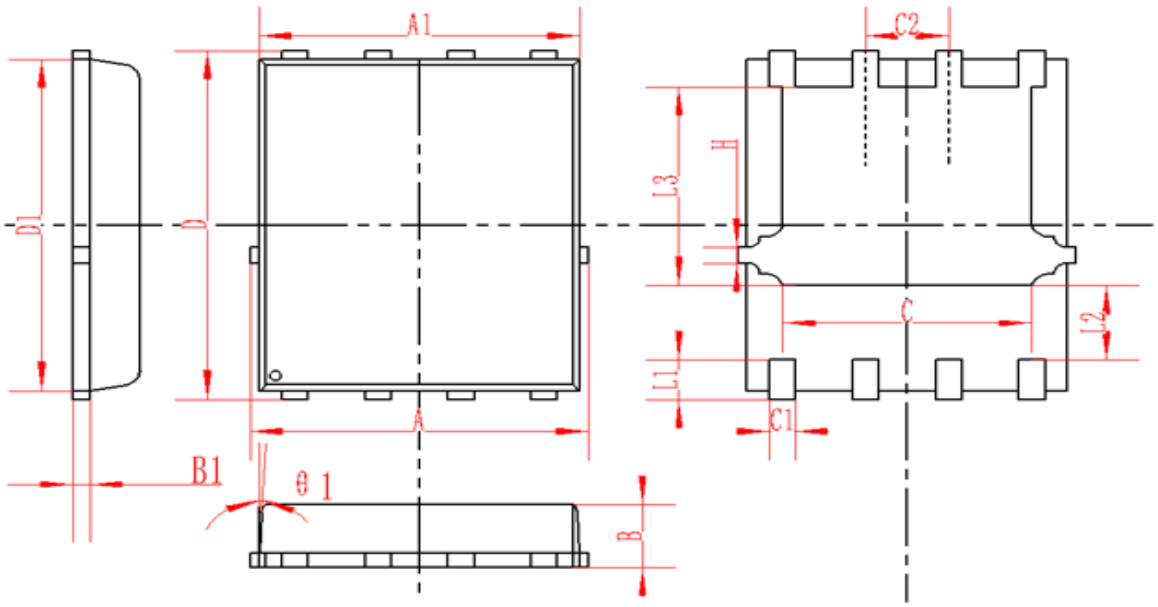


Figure 13: Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

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